

› MOLECULAIRE OPPERVLAKTEREINHEID VAN PRODUCTEN

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TNO innovation
for life

INHOUDSOPGAVE

MOLECULAIRE OPPERVLAKTEREINHEID VAN PRODUCTEN

› Waarom is het nodig?

- › Voorbeelden van moleculaire vervuiling
 - › EUV
 - › Proces van deze vervuiling
 - › TEM

› En wat is de aanpak?

- › Voorbeeld aan de hand van EBL2
- › Nieuwe reinheid richtlijn (VCCN richtlijn 12)

› Conclusie

EUV LITHOGRAFIE

- › Steeds kleinere microchips, met nieuwe lithografiemethode



Foto: ASML

- › EUV lithografie
- › Golflengte: 13,5 nm
- › In ultra-clean vacuüm
- › Spiegels in plaats van lenzen



Foto: Carl Zeiss
SMT

EUV LITHOGRAFIE

- › Steeds kleinere microchips, met nieuwe lithografiemethode

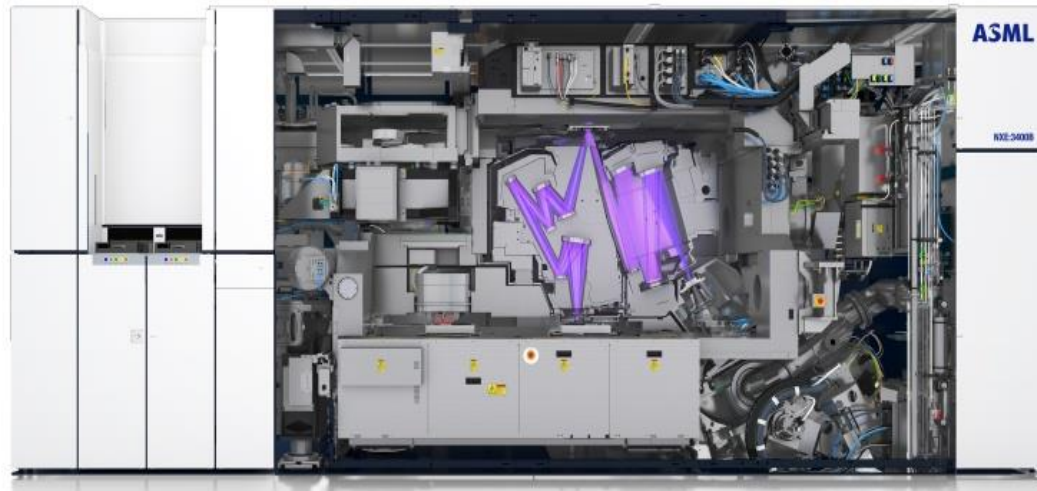


Foto: ASML

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- › **In ultra-clean vacuüm**
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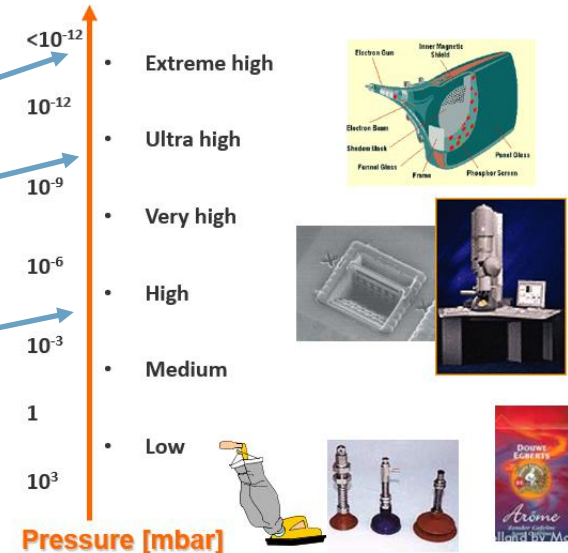


Foto: Carl Zeiss
SMT

VACUÛM

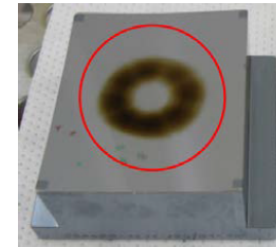
- › Een vacuüm is een ruimte zonder materie en zonder druk [wikipedia]
 - › In praktijk is een ruimte zonder druk en materie niet haalbaar
 - › 10^{-12} mbar heeft nog steeds 10^5 moleculen per cm^3
 - › 10^{-6} mbar geeft 1 monolaag aangroei per seconde

- › Vacuüm heeft vele toepassingsgebieden
 - › CERN en op de maan
 - › SEM
 - › TL lamp

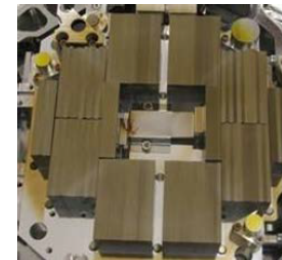


Carbon contamination

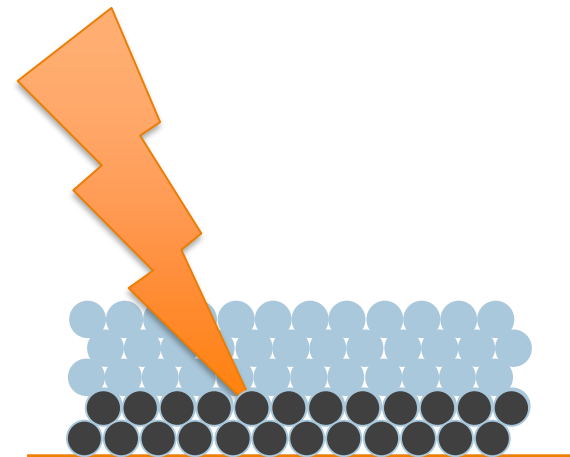
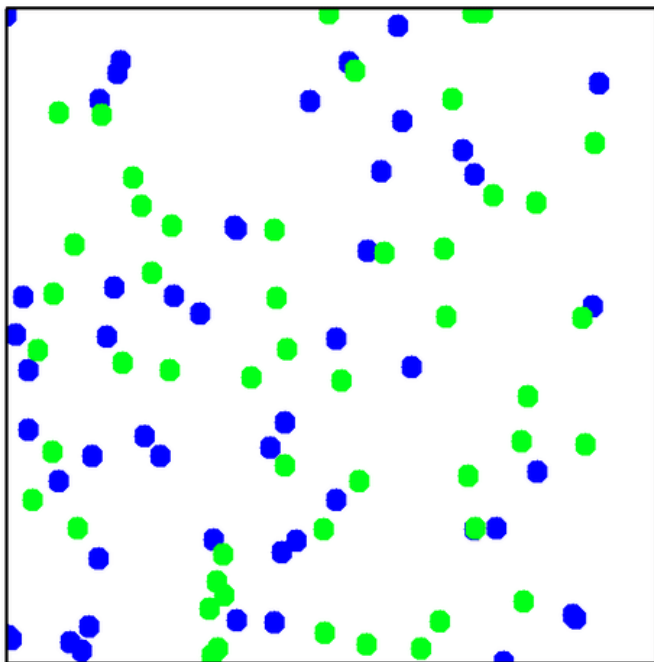
- ‘Vacuum’ contains residual (hydrocarbon) contaminants
- Hydrocarbons adsorb on (mirror) surfaces
- EUV photons and secondary electrons cause
 - Transformation of C_xH_y chains to aC:H
 - Reduction of H-content with irradiation dose
 - Radiation-induced outgassing of fragments
- EUV lifetime issue
 - How fast does carbon grow under actual tool conditions?



SEMATECH MET, 2007



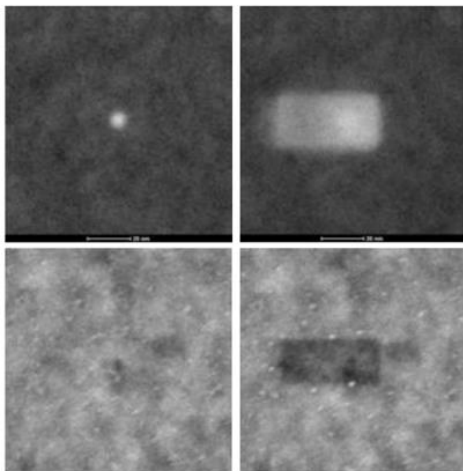
ADT mirror, 2007



Contamination measurement on TEM

Example:

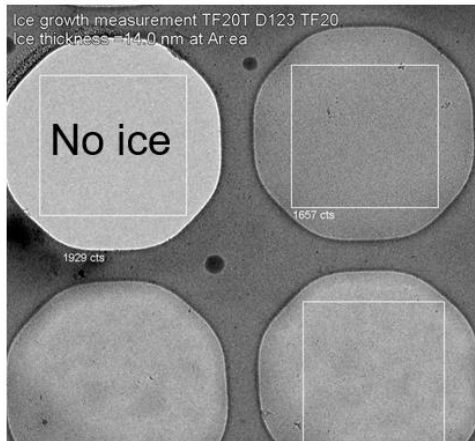
C_xH_y contamination level via Carbon Grown in STEM mode on sample



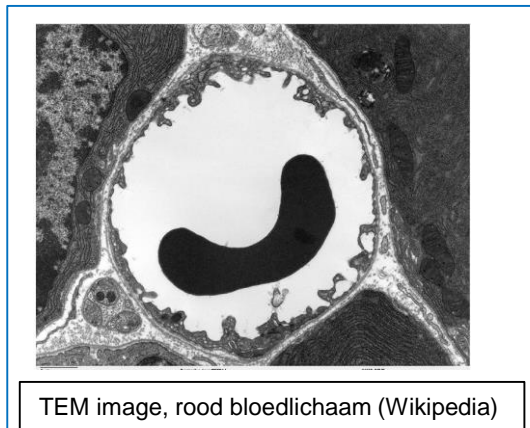
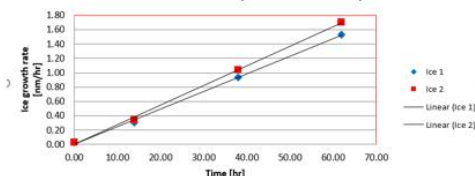
Measurement examples, contrast difference on SiN window of measuring sample @950 kx. Upper contaminated, lower clean (sample etching) Left reference image, right image after focus window.

Example:

H_2O contamination via Ice Grow on TEM Cryo sample, Transmission loss in time

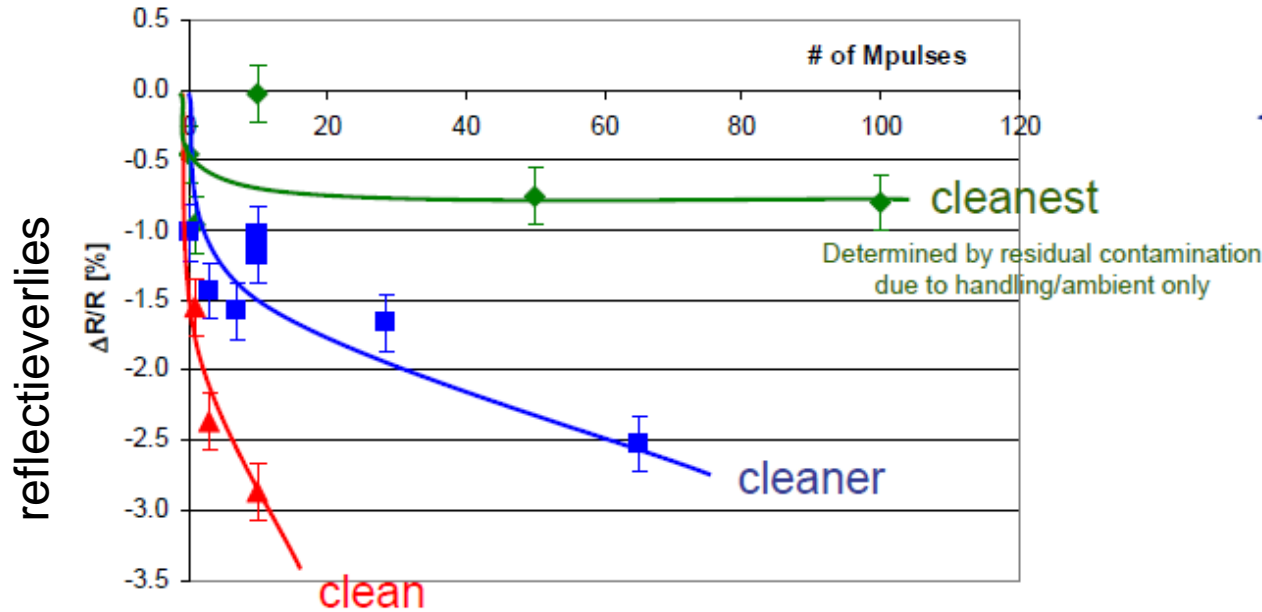


D Test = 0.02 nm/h and 0.03 nm/h



TEM image, rood bloedlichaam (Wikipedia)

Effect of environment on contamination rate was one of the early findings



2008

Ultra clean vacuüm

→ Large effect of vacuum cleanliness on carbon contamination

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VOORBEELD VAN AANPAK: EBL2

- › EBL2 is een onderzoeksfaciliteit van TNO die gebruikt wordt voor het onderzoeken van levensduur van onderdelen die aan EUV blootgesteld worden, dit door samples met EUV licht bloot te stellen
- › Hiervoor is een deeltjes arm, en ultraschoon vacuüm systeem nodig

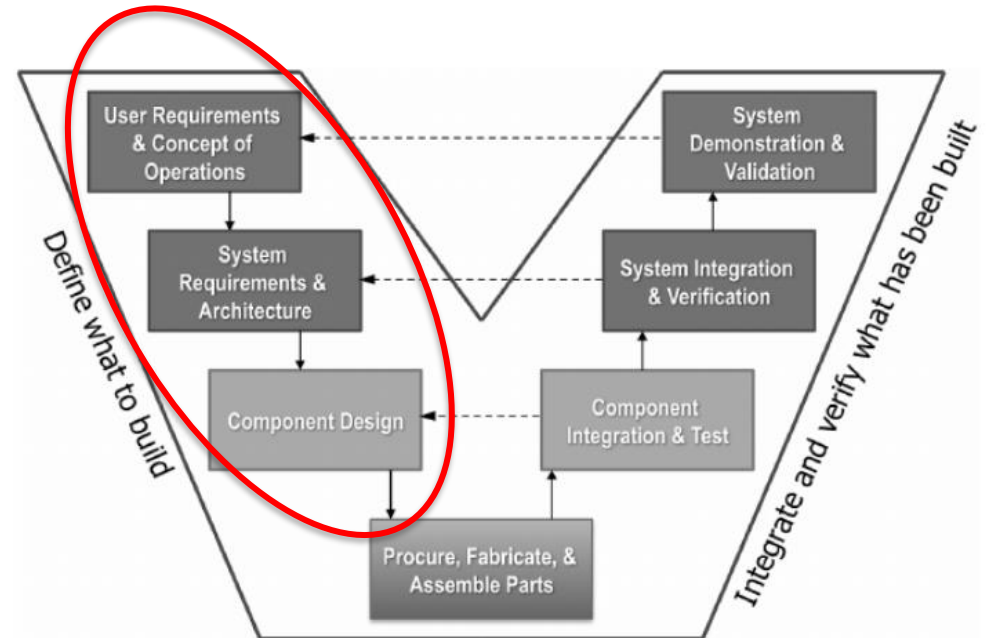


www.tno.nl/eb12

VERVUILINGSBUDGET

- › **Systeemaanpak**
 - › Vervuilingsbudget
 - › Waar, hoe schoon

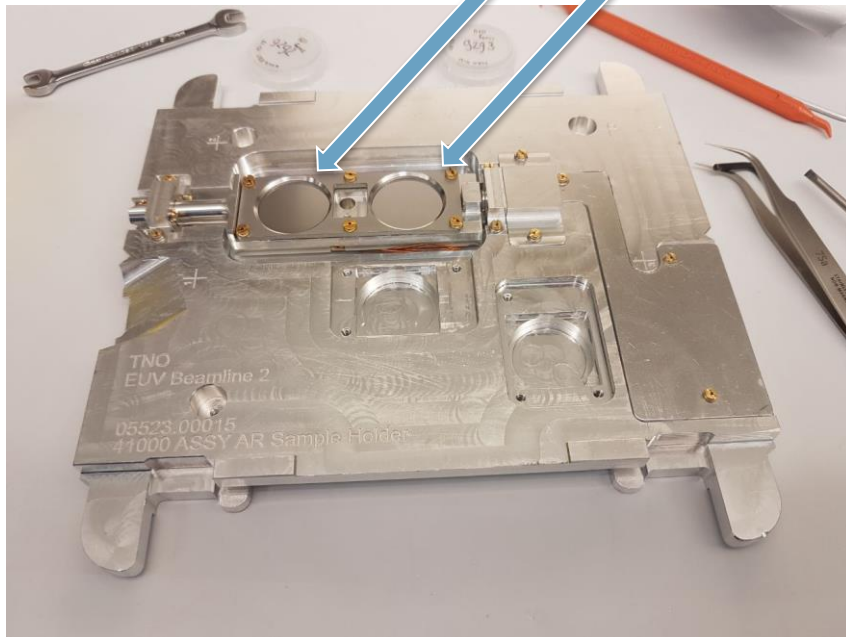
- › Sample route door EBL2



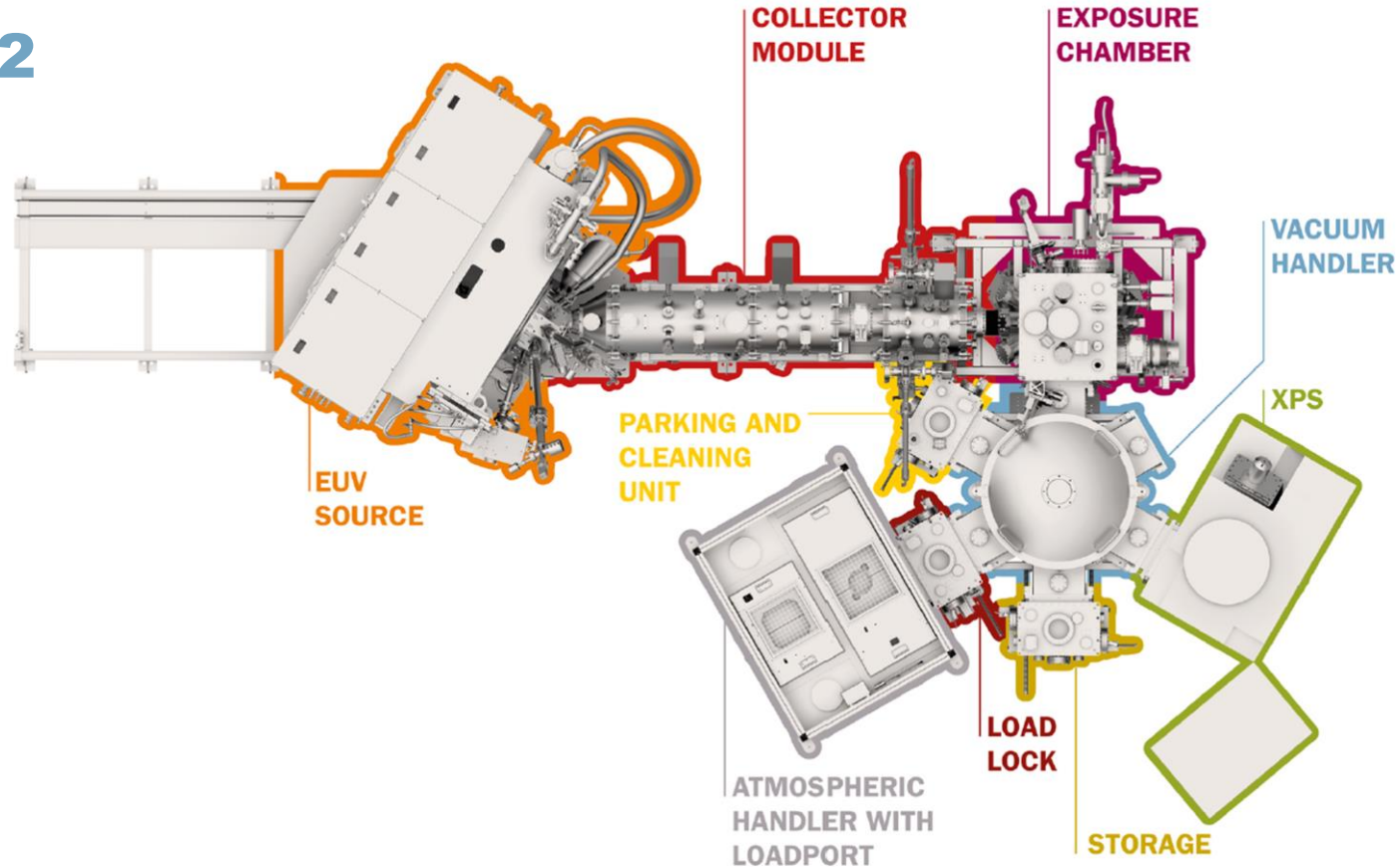
Sauser, Brian & Gove, Ryan & Forbes, Eric & Ramirez-Marquez, Jose. (2010). Integration maturity metrics: Development of an integration readiness level. Information Knowledge Systems Management. 9. 17-46.

EBL2

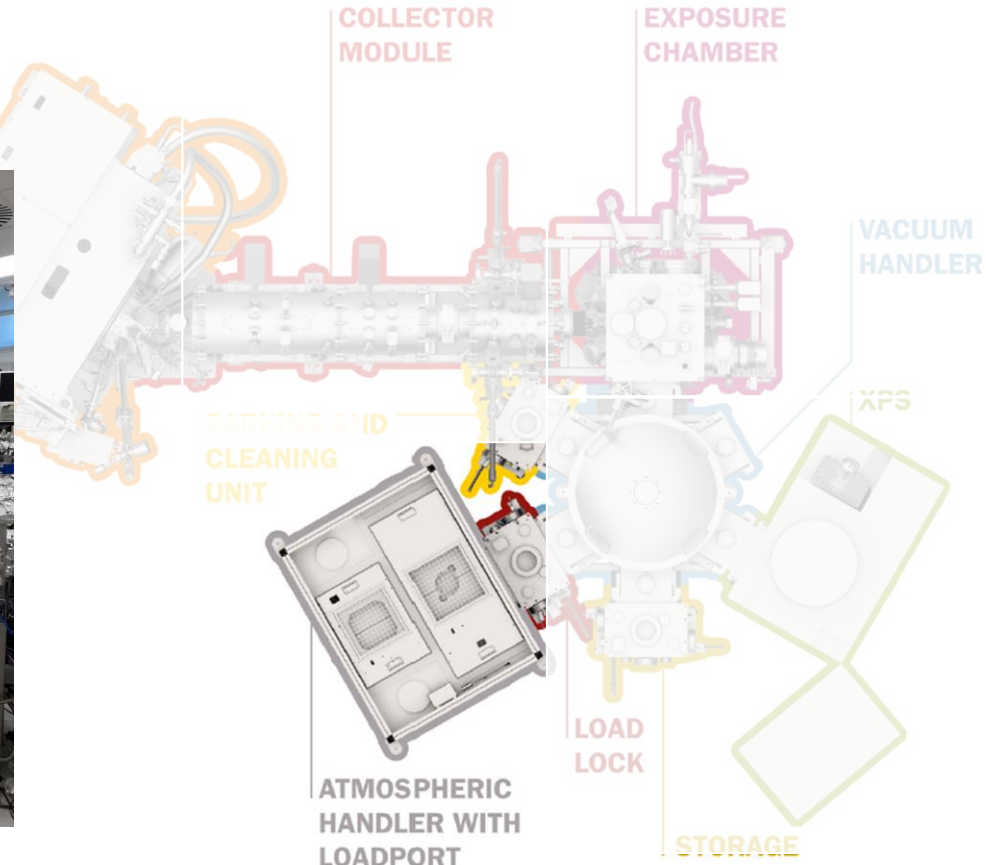
Samples



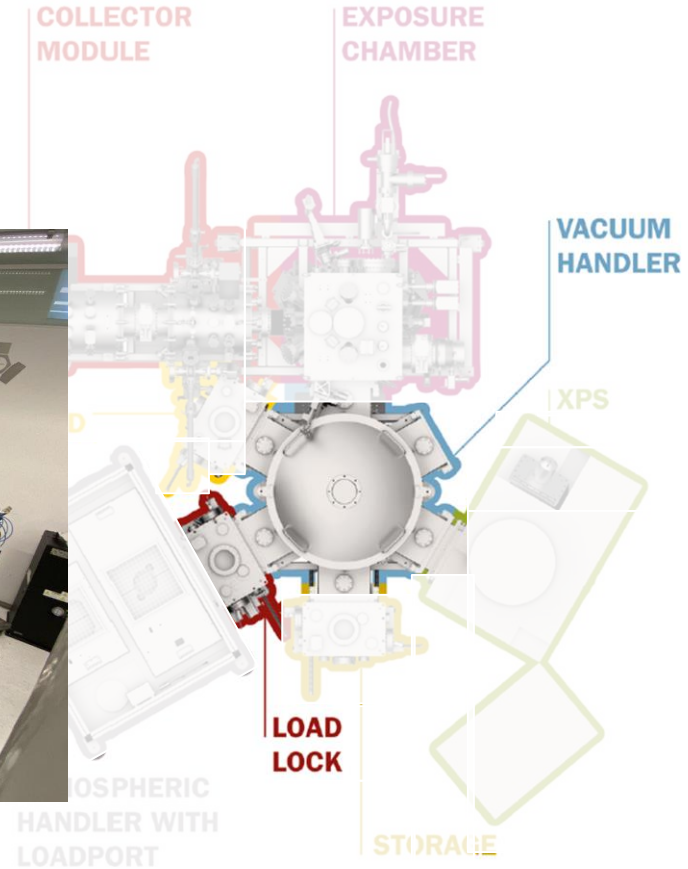
EBL2



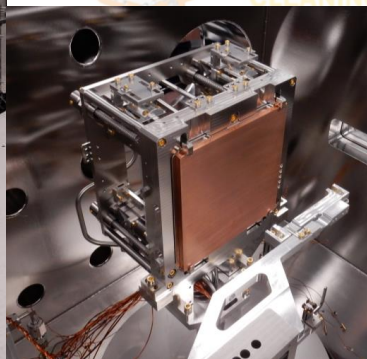
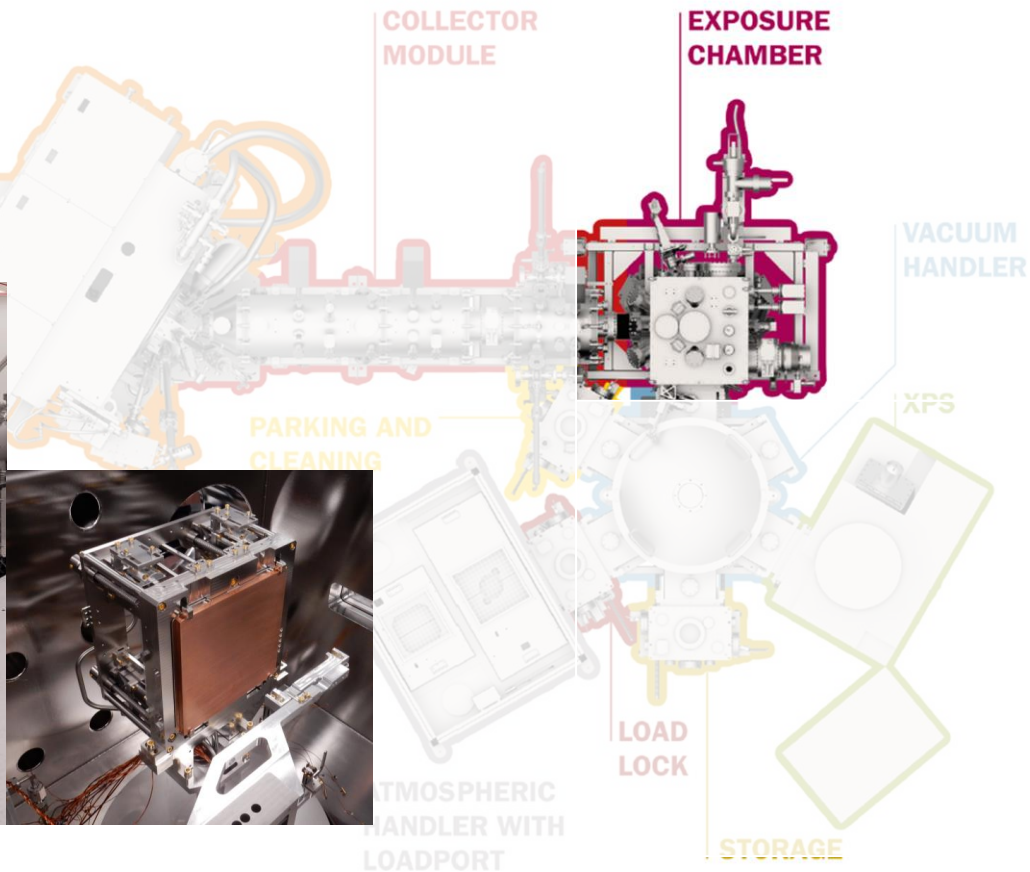
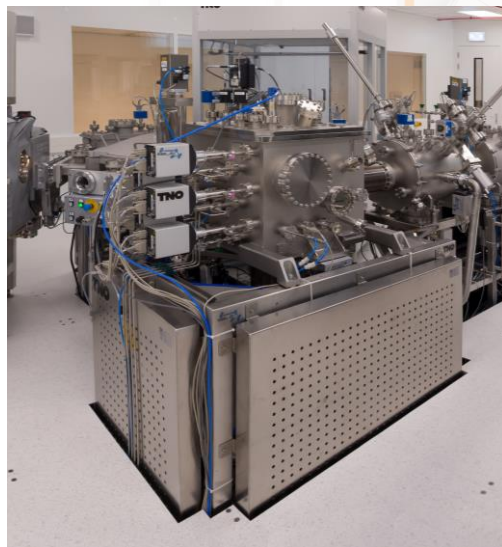
EBL2



EBL2



EBL2



EBL2 VACUÛM

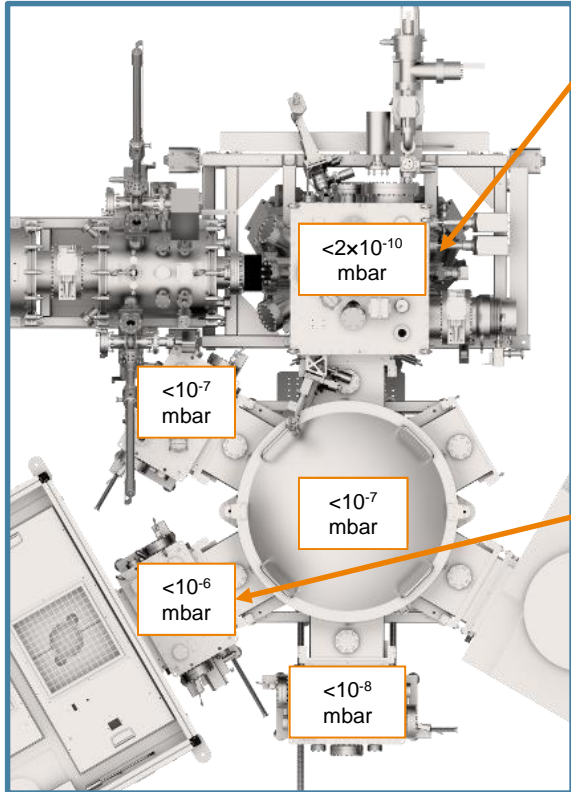


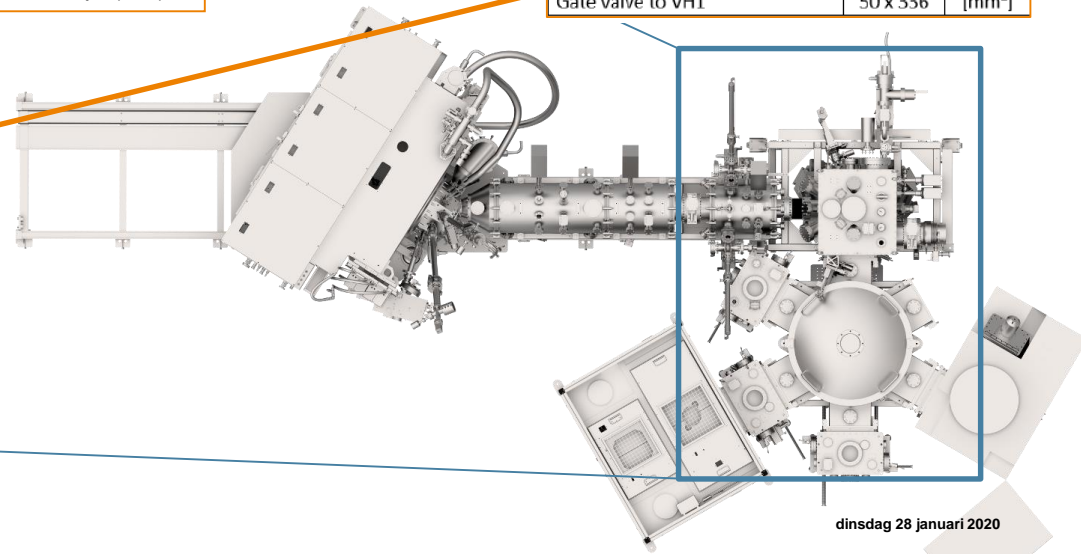
Table 4-9 Exposure Chamber qualification requirements

Requirement	Value	Unit
Total end pressure	$<1 - 2 \cdot 10^{-10}$	[mbar]
Partial pressure H ₂	$<10^{-10}$	[mbar]
Partial pressure H ₂ O	$<10^{-10}$	[mbar]
Partial pressure N ₂	$<10^{-12}$ (integrated)	[mbar]
Partial pressure O ₂		
Partial pressure C _x H _y 45-100		
Partial pressure - C _x H _y 101-200		
He leak rate	$<1 \cdot 10^{-10}$	[mbar.l/s]

Grade 1 cleaning, (extra schoon)
Verboden materialen lijst (HIO)

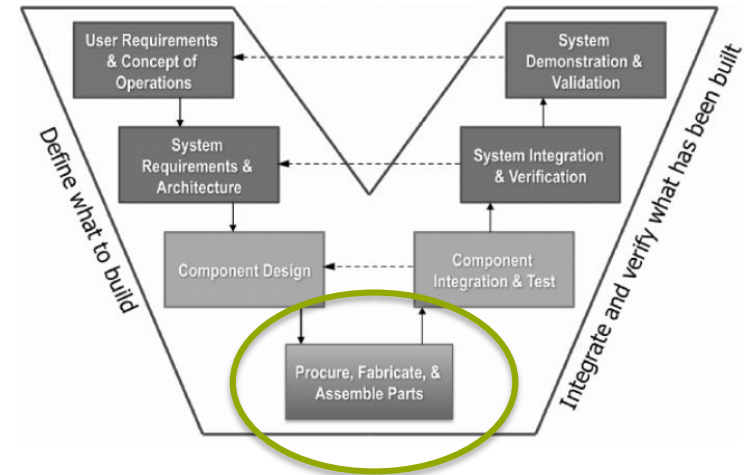
Table 4-2 Load Lock process requirements

Requirement	Value	Unit
Total pressure	$<10^{-6}$	[mbar]
Partial pressure H ₂	NA	
Partial pressure H ₂ O	NA	
Partial pressure N ₂	$<10^{-7}$	[mbar]
Partial pressure O ₂	$<10^{-8}$	[mbar]
Partial pressure C _x H _y 45-100	$<10^{-9}$	[mbar]
Partial pressure - C _x H _y 101-200	$<10^{-10}$	[mbar]
Partial pressure Ar	NA	
Partial pressure Xe	NA	
Evacuation (pump down) time	15-20	[min]
Gate valve to VH1	50 x 336	[mm ²]



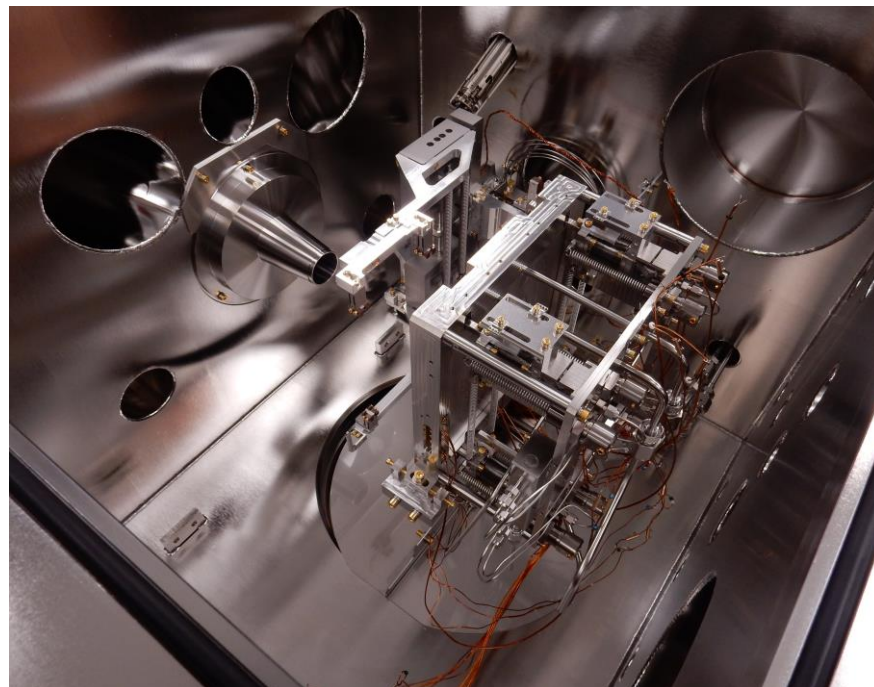
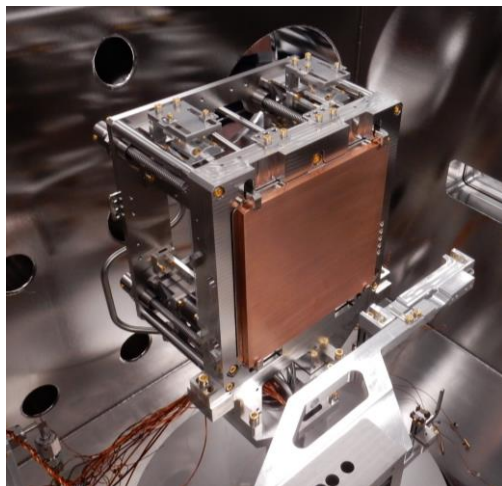
PRODUCTIE

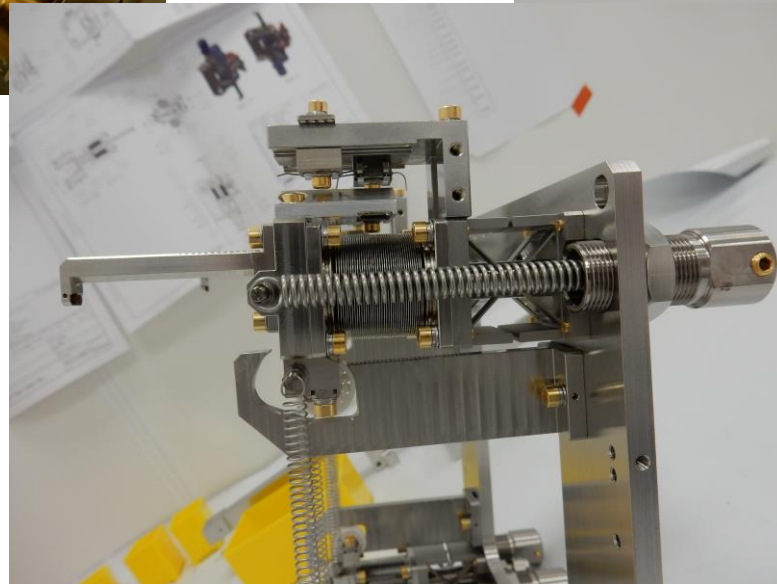
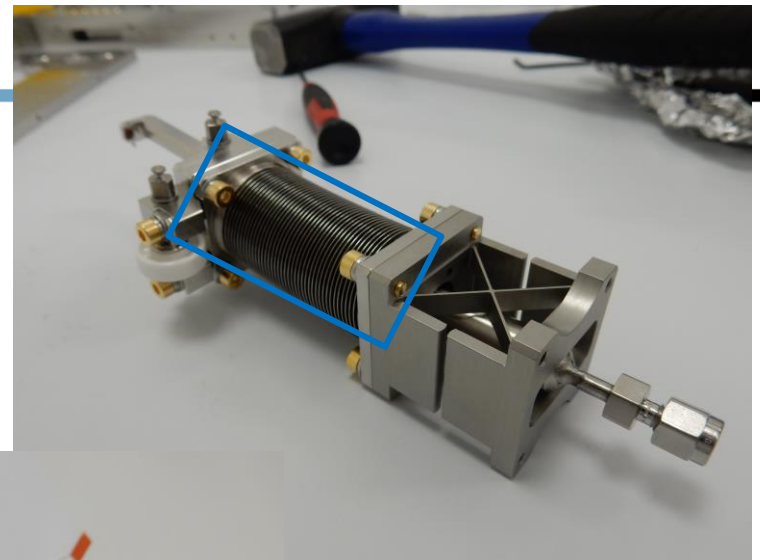
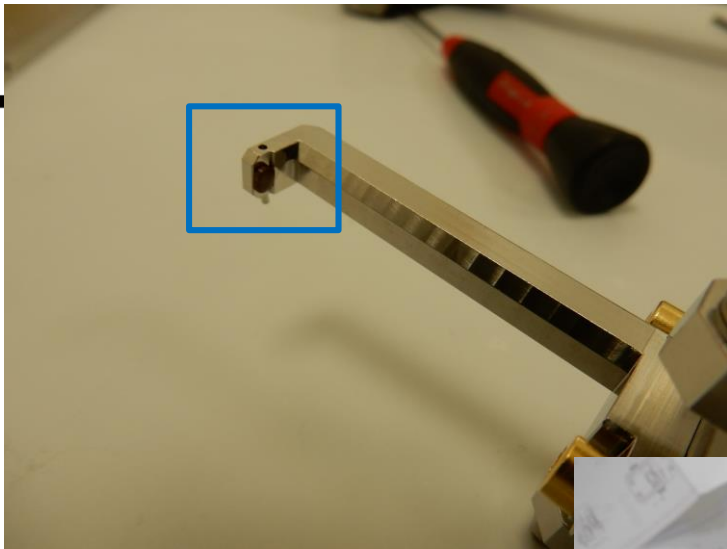
- › Materiaal en ontwerp moet reinigbaar zijn
 - › Bestendig tegen nat-chemisch reinigen
 - › Temperatuur bestendig
 - › Oppervlakken moeten bereikbaar zijn
- › Verspaningsmachines moeten schoon zijn
 - › Juiste koel- en smeermiddelen
 - › Geen tools gebruiken die in aanraking zijn geweest met materialen die niet toepasbaar zijn in vacuüm
- › Tijdens assemblage moet product schoon blijven
 - › Duidelijke instructie van personeel



PRODUCTIE / ONTWERP VOORBEELDEN

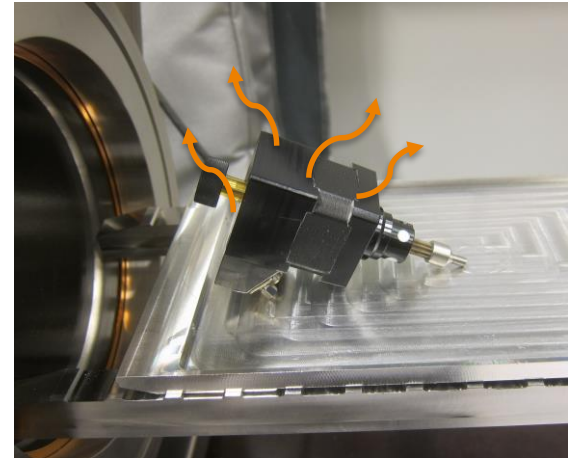
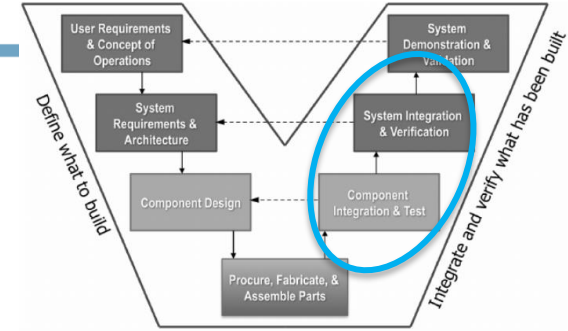
- › Sample handling in de exposurekamer
- › Strenge eisen op toegestane materialen
- › Onderdelen moeten reinigbaar zijn



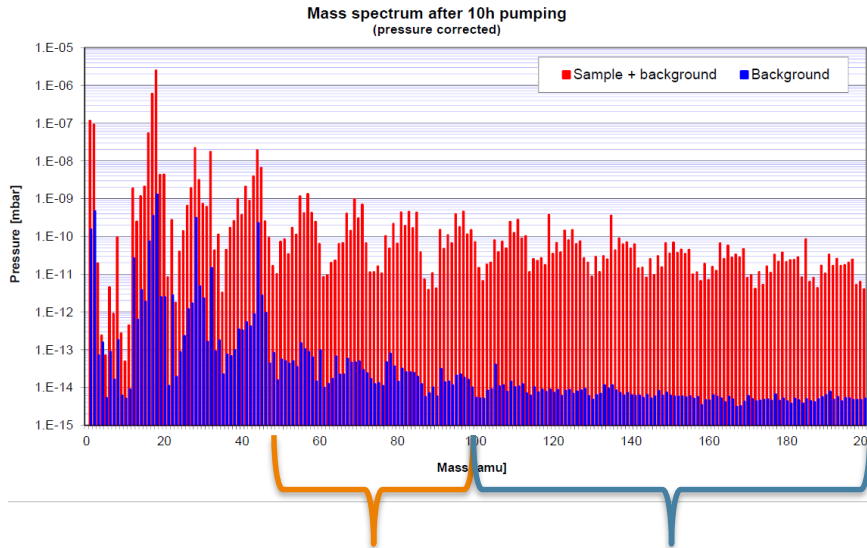




VALIDATIE REINHEID; UITGAS MEETOPSTELLING;



VALIDATIE UITGASSING

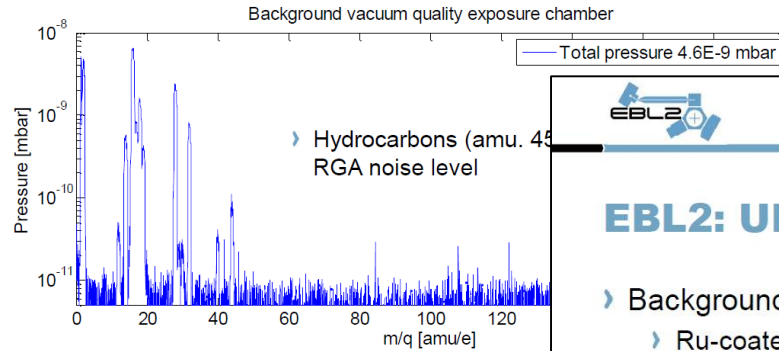


Test details			
Sample Id:	[REDACTED]	Pump speed [l.s ⁻¹]:	25
Description:	[REDACTED]	System:	ATOM
Date:	20-Nov-15	Ratio: IG/RGA	0.6
Data filename:	[REDACTED]	RGA Id:	QMA 422: SN 44248116
Background file:	[REDACTED]	Ion gauge Id:	IG (YEA07221)
Filename:	[REDACTED]		
Operator:	[REDACTED]		Sample Outgassing 200amu v7
Comments:	Black coated stepper motor with sub-D connector, no vents to prevent for virtual leakage, no apparent (visible) lubrication outside		

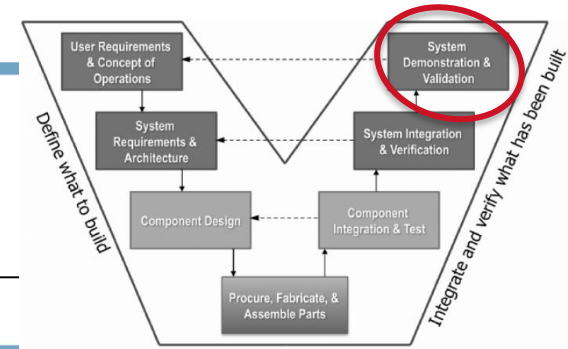
Outgassing rate at 1h:			Outgassing rate at 10h:		
	Sample (background subtracted)	(background)		Sample (background subtracted)	(background)
Q _{total} [mbar.l.s ⁻¹]	NA	7.50E-07	Q _{total} [mbar.l.s ⁻¹]	8.79E-05	7.50E-08
Q _{H₂O} [mbar.l.s ⁻¹]	NA	4.69E-07	Q _{H₂O} [mbar.l.s ⁻¹]	6.33E-05	3.30E-08
Q _{CxHy<101amu} [mbar.l.s ⁻¹]	NA	6.41E-10	Q _{CxHy<101amu} [mbar.l.s ⁻¹]	4.51E-07	1.40E-10
Q _{CxHy>100amu} [mbar.l.s ⁻¹]	NA	2.75E-11	Q _{CxHy>100amu} [mbar.l.s ⁻¹]	1.15E-07	1.72E-11
Q _{CxHy} [mbar.l.s ⁻¹]	NA	6.68E-10	Q _{CxHy} [mbar.l.s ⁻¹]	5.66E-07	1.57E-10
P _{ion gauge} [mbar]	NA	3.00E-08	P _{ion gauge} [mbar]	3.52E-06	3.00E-09
Comments:	High outgassing of H ₂ O and CxHy, traces of CxHy/fluorocarbons (119, 135, 185 amu), high O ₂ traces probably be due to virtual leakage				



EBL2: HIGH VACUUM QUALITY

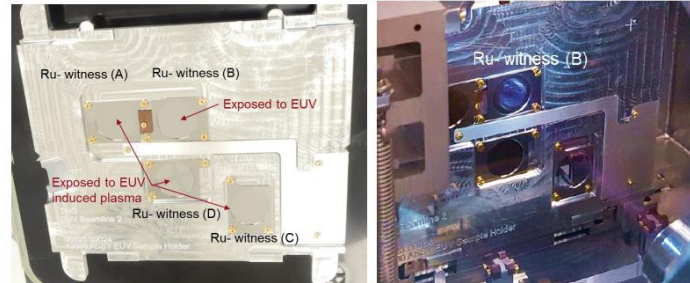


10 | EBL2 for mask lifetime testing



EBL2: ULTRA CLEAN SYSTEM

- Background screening of EBL2 exposure chamber
 - Ru-coated witness plates
 - 3kHz, 18 MShots, 15 mW/mm² in standard H₂ condition
 - XPS analysis without breaking vacuum



XPS results (at %) ; wide scan, without breaking vacuum				
Sample code	O	Ru / C	S	Sn
Ru-witness (A)	7.3	91.1	1.5	<
Ru-witness (B)	7.3	91.0	1.7	<
Ru-witness (C)	10.3	88.8	1.0	<
Ru-witness (D)	8.0	90.6	1.4	<

11 | EBL2 for mask lifetime testing

3/1/2016

EUV mask lifetime testing using EBL2; Chien-Ching Wu et.al. (TNO); 2018 SPIE Advanced Lithography

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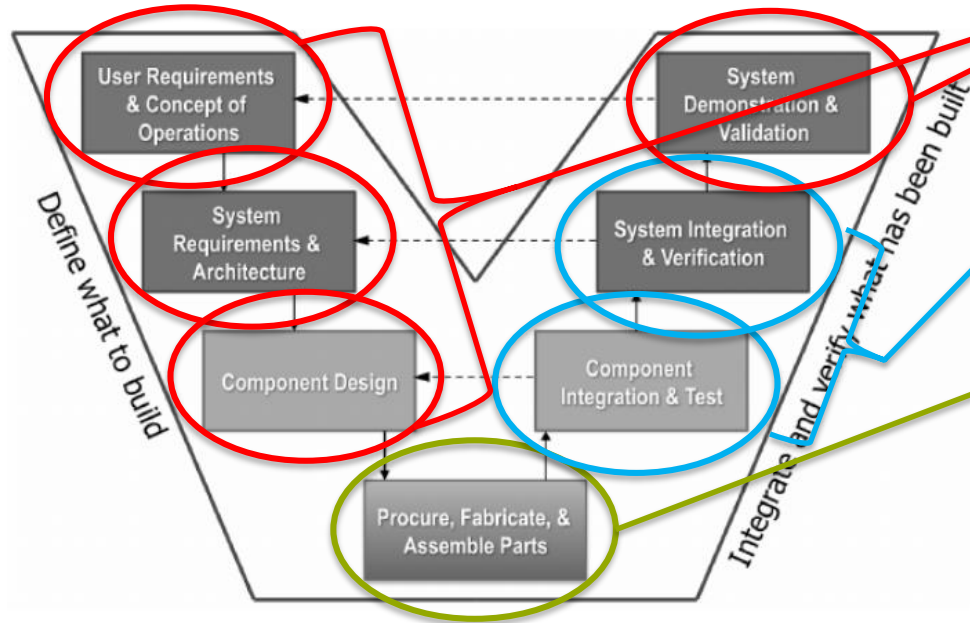
VCCN RICHTLIJN 12

Product/part cleanliness
with respect to particles and chemicals

specification, manufacturing, cleaning,
contamination control and qualification



VCCN RICHTLIJN 12



- 0 Introduction
- 1 Scope
- 2 Normative references
- 3 Terms and definitions
- 4 General outline of this guideline
- 5 Surface cleanliness specification
 - 5.1 General
 - 5.2 Surface cleanliness levels with respect to particles
 - 5.3 Surface cleanliness levels with respect to chemicals
 - 5.4 Surface cleanliness with respect to trace elements
- 6 Measurement methods
 - 6.1 General
 - 6.2 Surface cleanliness with respect to particles
 - 6.3 Cleanliness with respect to chemicals
- 7 Machining
 - 7.1 Raw materials
 - 7.2 Machine conditions
 - 7.3 Product handling
 - 7.4 Transport
 - 7.5 Surface treatment
- 8 Cleaning
 - 8.1 Cleaning methods
 - 8.2 Cleaning agents
 - 8.3 Evaluation of cleaning methods
- 9 Assembly
- 10 Clean controlled environment
 - 10.1 Contamination mechanisms
 - 10.2 Clean controlled environment
 - 10.3 Contamination control solutions
- 11 Packaging
- 12 Applications (best practises)
 - 12.1 Product cleanliness with respect to particles
 - 12.2 Product cleanliness with respect to chemicals
 - 12.3 Product cleanliness with respect to particles and chemicals

CONCLUSIE

- › In de toekomst zal er om steeds schonere producten gevraagd worden
- › Het is van groot belang om samen te werken om haalbare eisen op te stellen tegen reële kosten
- › **Acknowledgement**
 - › "If I have seen further it is by standing on the shoulders of Giants." - **Isaac Newton**
 - › "Great things in business are never done by one person. They're done by a team of people" – **Steve Jobs**

› **BEDANKT VOOR UW AANDACHT**

Voor meer inspiratie:
[TNO.NL/TNO-INSIGHTS](https://www.tno.nl/tno-insights)

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